



NPN Silicon Epitaxial Planar Transistor

KTD1304

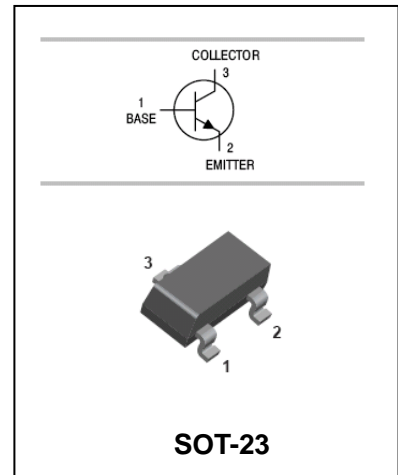
FEATURES

- High emitter-base voltage.
- High reverse h_{FE} .
- Low on resistance.



APPLICATIONS

- Audio muting application.



ORDERING INFORMATION

Type No.	Marking	Package Code
KTD1304	MAX	SOT-23

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current -Continuous	300	mA
I_B	Base Current	30	mA
P_C	Collector Power Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$



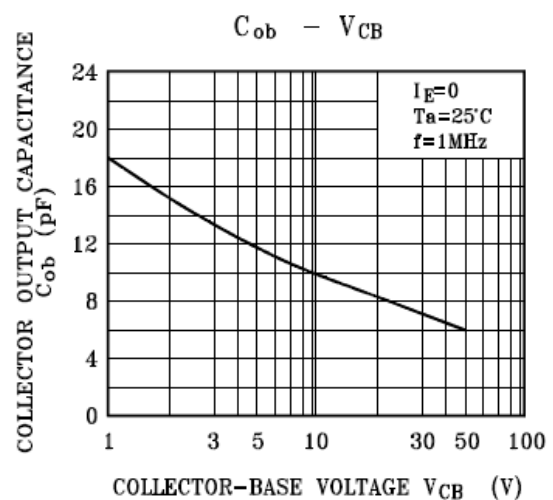
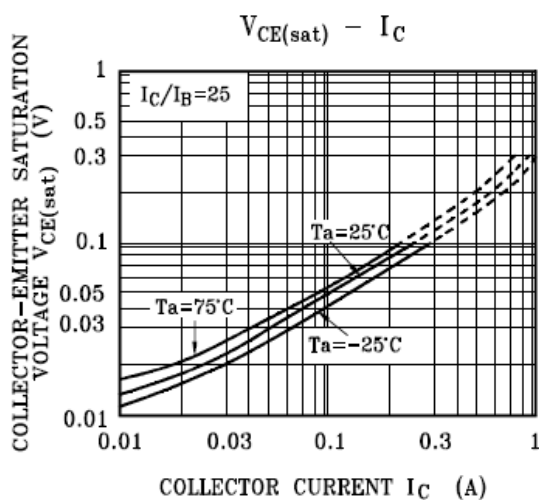
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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	12			V
Collector cut-off current	I_{CBO}	$V_{CB}=25V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=12V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=2V, I_C=4mA$	200		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=1mA$		60		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			10	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



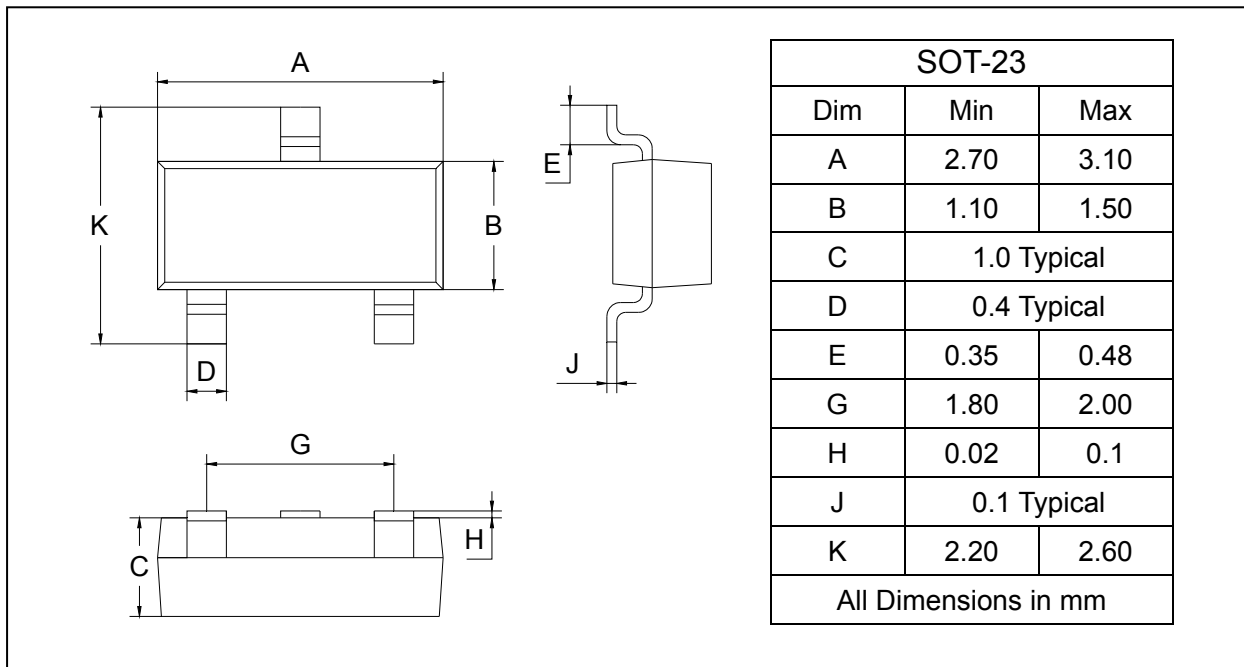
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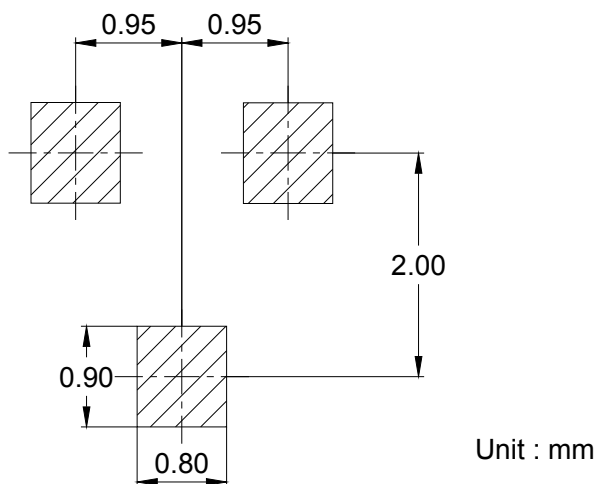
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
KTD1304	SOT-23	3000/Tape&Reel